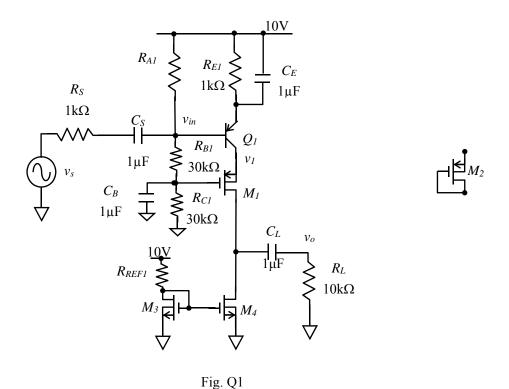
### NATIONAL UNIVERSITY of SINGAPORE

#### **Department of Electrical and Computer Engineering**

## EE2021 – Devices and Circuits Tutorial 5 Solutions

Q1.



In the two-stage amplifier circuit shown in Fig. Q1, assume that the pnp BJT, the NMOS transistors and the PMOS transistors have the following device parameters:

- $V_A = 100 \text{ V}$  and  $\beta = 100 \text{ for the BJT}$ ,  $Q_I$ ;
- $K_n = 2 \text{m A/V}^2$ ,  $V_{THN} = 1 \text{ V}$ ,  $\lambda_n = 0.001 \text{ V}^{-1}$  and no body effect for the NMOS transistors,  $M_3$  and  $M_4$ .
- $K_p = 2 \text{ m A/V}^2$ ,  $V_{THP} = -1 \text{ V}$ ,  $\lambda_p = 0.001 \text{ V}^{-1}$  and no body effect for the PMOS transistors,  $M_I$  and  $M_2$ .
- (a) Identify the configuration of each stage of the multi-stage amplifier.
- (b) Design  $R_{REF1}$  such that  $M_1$ ,  $M_3$  and  $M_4$  each has a drain current of 1 mA assuming these transistors are operating in the saturation region.
- (c) Estimate the small signal parameters of  $M_1$ , i.e.  $g_{m,M1}$ , and  $r_{o,M1}$  and the small signal parameters of  $Q_1$ , i.e.,  $g_{m,Q1}$ ,  $r_{\pi,Q1}$ ,  $r_{o,Q1}$ , assuming the value of the drain current in part (b).
- (d) Design  $R_{A1}$  to ensure that  $M_1$ ,  $M_3$  and  $M_4$  each has a drain current of 1 mA assuming these transistors are operating in the saturation region.
- (e) Estimate the overall gain, i.e.,  $v_o/v_s$ .
- (f) Diode connected transistor M<sub>2</sub> shown in the right of Fig. Q1 can be used to replace R<sub>E1</sub>. Comment whether the overall gain will be affected and if the gain is affected, which component values need to be changed to restore the gain in part (e).

- 1. (a) Identify the configuration of each stage of the multi-stage amplifier. CE-CG
  - (b) Design  $R_{REF1}$  such that  $M_1$ ,  $M_3$  and  $M_4$  each has a drain current of 1 mA.

$$I_D = K_n (V_{GS,M3} - V_{THN})^2 = 1mA \Rightarrow V_{GS,M3} = 1.71$$

$$R_{REF1} = \frac{10 - V_{GS,M3}}{1mA} = 8.3k$$

Note that the other solution,  $V_{GS,M3} = 0.29 \text{ V}$  is not applicable as it is less than  $V_{THN}$  and so the MOSFET is off.

(c) Estimate the small signal parameters of  $M_1$ , i.e.  $g_{m\_M1}$ , and  $r_{o\_M1}$  and the small signal parameter of  $Q_1$ , i.e.  $g_{m\_Q1}$ ,  $r_{\pi\_Q1}$ ,  $r_{\sigma\_Q1}$  assuming the value of the drain current in (b).

$$g_{m,M1} = 2.8mA/V, r_{o,M1} = 1M$$
  
 $g_{m,O1} = 40mA/V, r_{\pi,O1} = 2.5k, r_{o,O1} = 100k$ 

(d) Design R<sub>A1</sub> such that the circuit can function properly.

$$V_{E,Q1} = 10 - 1mA \times 1k = 9V$$
  
 $V_{B,Q1} = 9 - 0.7 = 8.3V = 10 \times \frac{60k}{60k + R_{A1}}$   
 $\Rightarrow R_{A1} = 12.3k$ 

(e) Estimate the overall gain, i.e.,  $v_o/v_s$ .

$$\frac{v_o}{v_s} = \frac{R_{A1} // R_{B1} // r_{\pi,Q1}}{R_S + R_{A1} // R_{B1} // r_{\pi,Q1}} \times g_{m,Q1} \frac{1}{g_{m,M1}} \times g_{m,M1} R_L$$

$$= 0.66 \times 14.3 \times 28 = 264$$

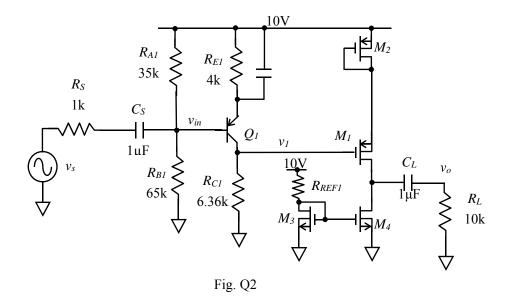
(f) Diode connected M<sub>2</sub> as shown in the right of Fig. Q1 can be used to replace R<sub>E1</sub>. Comment whether the overall gain will be affected and if the gain is affected, which component values need to be changed.

Yes, it will be affected because the biasing of  $Q_1$  would not be correct. To ensure the proper biasing,  $R_{A1}$  needs to be changed. Given that  $|V_{GS,M2}|=1.71$  for  $I_D=1$ mA,  $V_{B,Q1}=10-1.71-0.7=7.59$ . Hence,

$$V_{B,Q1} = 7.59V = 10 \times \frac{60k}{60k + R_{A1}}$$
  
 $\Rightarrow R_{A1} = 19k$ 

By modifying  $R_{A1}$ , all the biasing will be the same as earlier case, and the gain will remain unchanged.

Q2.



In the two-stage amplifier circuit shown in Fig. Q2, assume that the pnp BJT, the NMOS and the PMOS have the following device parameters:

- $V_A = 100 \text{ V}$  and  $\beta = 100 \text{ for the BJT}$ ,  $Q_I$ ;
- $K_n = 2 \text{m A/V}^2$ ,  $V_{THN} = 1 \text{ V}$ ,  $\lambda_n = 0.001$  and no body effect for the MOSFETs,  $M_3$  and  $M_4$ .
- $K_p = 2 \text{m A/V}^2$ ,  $V_{THP} = -1 \text{ V}$ ,  $\lambda_p = 0.001$  and no body effect for the MOSFETs,  $M_1$  and  $M_2$ .
- (a) Identify the configuration of each stage of the multi-stage amplifier.
- (b) Estimate the collector current for  $Q_I$  and its corresponding small signal parameter, i.e.  $g_{m\_QI}$ ,  $r_{\pi\_QI}$ ,  $r_{o\_QI}$ .
- (c) Design  $R_{REF1}$  such that  $M_1$ ,  $M_3$ ,  $M_4$  and  $M_2$  each has a drain current of 3 mA.
- (d) Estimate the small signal parameters of  $M_I$ , i.e.  $g_{m\_MI}$ , and  $r_{o\_MI}$  assuming the value of the drain current in (c).
- (e) Estimate the overall gain, i.e.,  $v_o/v_s$ .
- (g)  $M_2$  can be replaced with an NMOS transistor. Show part of the new circuit including only  $M_1$ ,  $M_2$  and  $V_{DD}$  but with  $M_2$  replaced using NMOS transistor. Comment on the effect on the overall gain with reasoning.
- 2. (a) Identify the configuration of each stage of the multi-stage amplifier.

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(b) Estimate the collector current for Q1 and its corresponding small signal parameter, i.e.  $g_{m\_Q1}$ ,  $r_{\pi\_Q1}$ ,  $r_{o\_Q1}$ .

$$\begin{split} V_{B,Q1} &= 10 \times \frac{65}{100} = 6.5V \\ V_{E,Q1} &= V_{B,Q1} + 0.7 = 7.2V \\ I_C &\approx I_E = \frac{10 - 7.2}{4k} = 0.7 mA \\ I_B &= 7 \mu A << I_{RA1}, I_{RB1} = 100 \mu A \\ g_{m,Q1} &= 28 mA/V, r_{\pi,Q1} = 3.57 k, r_{o,Q1} = 143 k \end{split}$$

(c) Design  $R_{REF1}$  such that  $M_1$ ,  $M_3$ ,  $M_4$  and  $M_2$  each has a drain current of 3 mA.

$$I_D = K_n (V_{GS,M3} - V_{THN})^2 = 3mA \Rightarrow V_{GS,M3} = 2.22 V$$

$$R_{REF1} = \frac{10 - V_{GS,M3}}{3mA} = 2.59k$$

Note that the other solution,  $V_{GS,M3} = -0.22 \text{ V}$  is not applicable as it is less than  $V_{THN}$  and so the MOSFET is off.

(d) Estimate the small signal parameters of  $M_1$ , i.e.  $g_{m\_M1}$ , and  $r_{o\_M1}$  assuming the value of the drain current in (c).

$$g_{m,M1} = 2\sqrt{K_n I_D} = 4.9 \text{ mA/V}$$
 $r_{o,M1} = \frac{1}{\lambda_n I_D} = 333 \text{ k}$ 

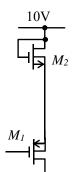
(e) Estimate the overall gain, i.e.,  $v_o/v_s$ .

$$A_{V} = \frac{R_{A1} // R_{B1} // r_{\pi,Q1}}{R_{A1} // R_{B1} // r_{\pi,Q1} + R_{S}} \times g_{m,Q1} R_{C1} \times \frac{g_{m,M1}}{1 + g_{m,M1}} \frac{1}{g_{m,M2}} R_{L}$$

$$= 0.76 \times 28m6.09k \times 2.45m10k = 3175$$

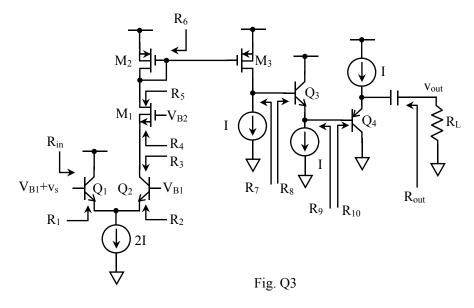
(f) M<sub>2</sub> can be replaced with an NMOS transistor. Show part of the new circuit including only M<sub>1</sub>, M<sub>2</sub> and V<sub>DD</sub> but with M<sub>2</sub> replaced using NMOS transistor. Comment on the effect on the overall gain with reasoning.

The gain would not be affected because both NMOS and PMOS have identical characteristic.

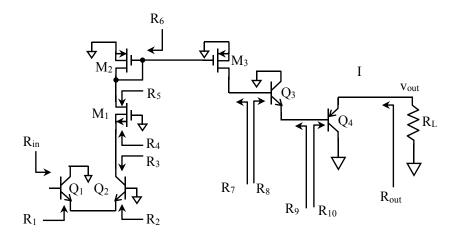


Q3. Analyze the following circuit. Write down the expressions for all the equivalent resistances ( $R_{I-}$   $R_{I0}$ ,  $R_{in}$ ,  $R_{out}$ ). All expressions must be in terms of transistor small signal parameters. Neglect body effect.

(Hints: Some of the resistances are inter-dependent, so some resistances need to be worked out first before other resistances can be solved.)



# **3.** AC equivalent circuit :



$$R_{10} = r_{\pi,Q4} (1 + g_{m,Q4} R_L)$$
 [Table 1 Configuration A]

$$\begin{split} R_8 &= r_{\pi,Q3} \Big( 1 + g_{m,Q3} R_{10} \Big) \quad \begin{bmatrix} Table & 1 & Configuration & A \end{bmatrix} \\ &= r_{\pi,Q3} \Big[ 1 + g_{m,Q3} r_{\pi,Q4} \Big( 1 + g_{m,Q4} R_L \Big) \Big] \end{split}$$

$$R_7 = r_{o.M.3}$$
 [Table 2 Configuration B]

$$R_9 = \frac{1}{g_{m,O3}} + \frac{R_7}{\beta + 1} = \frac{1}{g_{m,O3}} + \frac{r_{o,M3}}{\beta + 1}$$
 [Table 1 Configuration C]

$$R_{out} = \frac{1}{g_{m,Q4}} + \frac{R_9}{\beta + 1} = \frac{1}{g_{m,Q4}} + \frac{1}{\beta + 1} \left[ \frac{1}{g_{m,Q3}} + \frac{r_{o,M3}}{\beta + 1} \right] \quad [Table \ 1 \ Configuration \ C]$$

$$R_1 = \frac{1}{g_{m,Q_1}}$$
 [Table 1 Configuration C]

$$\begin{split} R_3 &= r_{o,Q2} \Big[ 1 + g_{m,Q2} \Big( r_{\pi,Q2} / / R_1 \Big) \Big] \quad \begin{bmatrix} Table & 1 & Configuration & B \end{bmatrix} \\ &= r_{o,Q2} \Bigg[ 1 + g_{m,Q2} \left( r_{\pi,Q2} / / \frac{1}{g_{m,Q1}} \right) \right] \approx 2 r_{o,Q2} \quad \begin{bmatrix} \because g_{m,Q1} = g_{m,Q2} \end{bmatrix} \end{split}$$

$$R_5 = r_{o,M1} (1 + g_{m,M1} R_3) = r_{o,M1} (1 + 2g_{m,M1} r_{o,Q2})$$
 [Table 2 Configuration B]

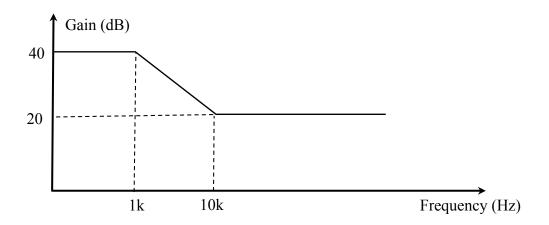
$$R_6 = \frac{1}{g_{mM2}} / / R_5 \approx \frac{1}{g_{mM2}}$$
 [Table 2 Configuration E]

$$R_4 = \frac{1}{g_{m,M1}} \frac{r_{o,M1} + \frac{1}{g_{m,M2}}}{r_{o,M1}} \approx \frac{1}{g_{m,M1}} [Table \ 2 \ Configuration \ D]$$

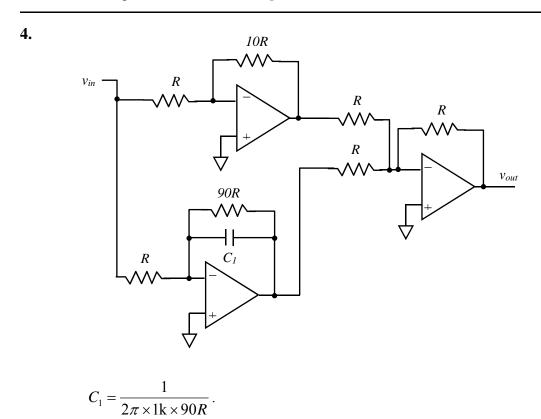
$$R_{2} = \frac{1}{g_{m,Q2}} \frac{r_{o,Q2} + R_{4}}{r_{o,Q2} + \frac{R_{4}}{\beta}} \approx \frac{1}{g_{m,Q2}} \quad [Table \ 1 \ Configuration \ D]$$

$$R_{in} = r_{\pi,Q1} (1 + g_{m,Q1} R_2) \approx 2r_{\pi,Q1}$$
 [Table 1 Configuration A]

**Q4.** Show an opamp circuit that can generate the following transfer in Fig. Q4:



[Note : Gain(dB) =  $20 \times \log_{10}(V_{out}/V_{in})$ . Hence, 40dB is equivalent to  $V_{out}/V_{in}=100$ , 20dB is equivalent to  $V_{out}/V_{in}=10$ ]



**Q5**. (a) Derive  $R_x$  in the circuit shown in Fig. Q5a. (Note that  $v_I$  is a voltage dependent voltage source and  $R_x = v_x / i_x$ .)

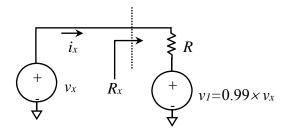
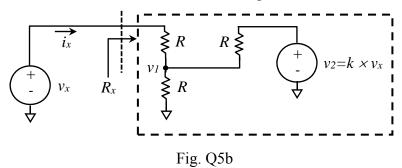


Fig. Q5a

(b) Derive the value k for the circuit shown in Fig. Q5b such that  $v_1 = 0.99v_x$ .

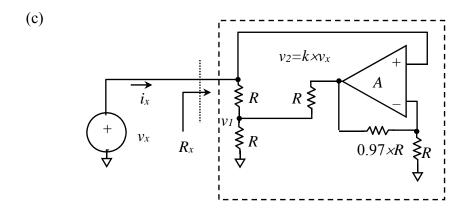


- (c) Design an opamp circuit that can realize circuit within the dash box in part (b). You can treat  $v_x$  as independent signal source.
- (d) The circuit in part (c) is known as a resistance multiplier. It can realize huge resistance with relatively small resistor values. Suggest and show a simple filtering circuit that can make use of this technique.
- **5.** (a) Apply ohms law for resistor R

$$i_x = \frac{v_x - 0.99v_x}{R} = \frac{0.01v_x}{R} \Rightarrow R_x = \frac{v_x}{i_x} = 100R.$$

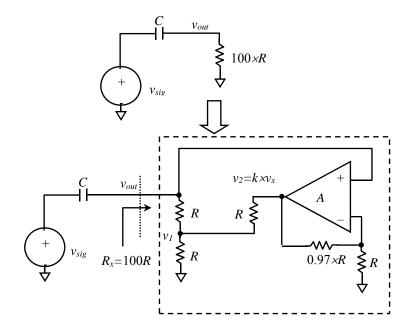
(b) Apply KCL at point  $v_I$ , and assume  $v_I = 0.99v_x$  according to part (a).

$$\frac{v_x - 0.99v_x}{R} + \frac{kv_x - 0.99v_x}{R} = \frac{0.99v_x}{R} \Rightarrow k = 1.97$$
.



Since  $v_2 = kv_x$  where k is a positive value of 1.97, if you search through the opamp library, you can see that the non-inverting amplifier fits the requirement. Hence, we replace the  $v_2 = kv_x$  with a non-inverting amplifier.

(d) As illustrated in part (c), the circuit in the dashed box presents a resistance of 100R between one port and ground, hence we can use the circuit in the dashed box to replace a resistor that is connected between one point and ground. This implies that a passive high pass filter with the resistor connected between one point ( $v_{out}$ ) and ground can be used as shown below.



- **Q6.** You are given a task to build an arbitrary signal generator. You may assume that a square wave voltage source is readily available.
  - (a) Show an opamp circuit that can produce a triangular wave from a square wave input with 50% duty cycle, i.e.  $T_{POS} = T_{NEG}$ , as shown in Fig. Q6a.

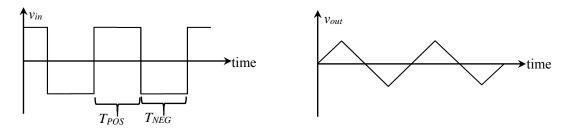
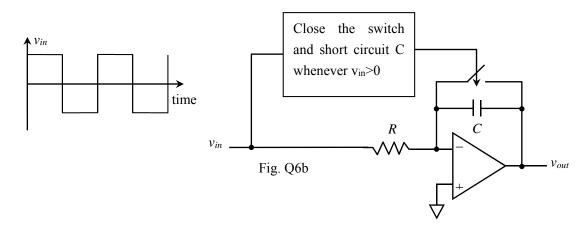


Fig. Q6a

(b) Consider the opamp circuit shown in Fig.Q6b. The switch will short circuit the capacitor whenever the input voltage is positive. Sketch the output waveform (*vout*) when the input is a square wave with 50% duty cycle.



(c) Show an opamp circuit that can produce a saw tooth wave from a square wave input with 50% duty cycle as shown in Fig. Q6c.

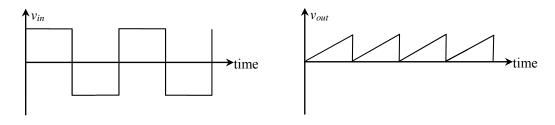
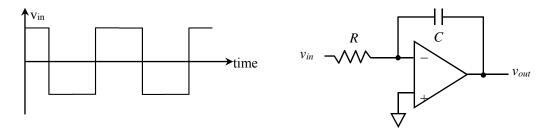
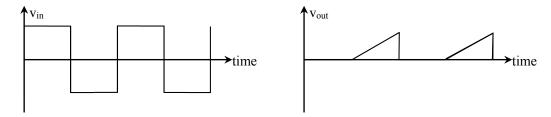


Fig. Q6c

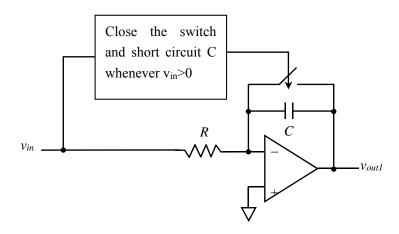
- **6.** You are given a task to build an arbitrary signal generator. You may assume that a square wave voltage source is readily available.
  - (a) Show an opamp circuit that can produce a triangular wave from a square wave input with 50% duty cycle, i.e.  $T_{POS}=T_{NEG}$ , as shown in Fig. Q6a.

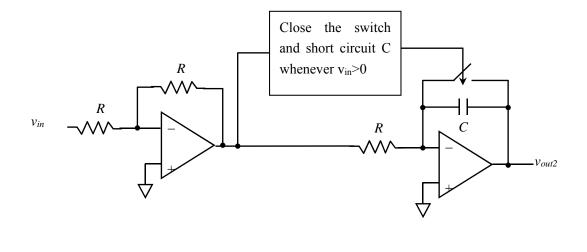


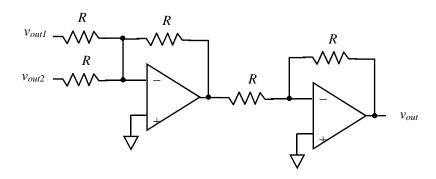
(b) Consider the opamp circuit shown in Fig.Q6b. The switch will short circuit the capacitor whenever the input voltage is positive. Sketch the output waveform (*v*<sub>out</sub>) when the input is a square wave with 50% duty cycle.



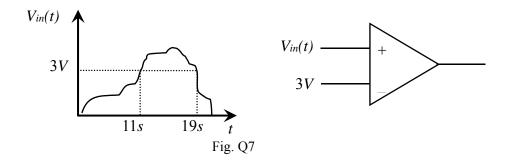
(c) Show an opamp circuit that can produce a saw tooth wave from a square wave input with 50% duty cycle as shown in Fig. Q6c.







- Q7. (a) Draw an opamp circuit that can convert a square wave to a triangular wave.
  - (b) Consider the comparator circuit shown in Fig. Q7. Sketch the comparator output waveform for the given input waveform. Indicate clearly the timing and voltage information. You may assume that the maximum and minimum output voltages of the comparator are +5V and -5V, respectively.



(c) Propose an opamp-based circuit that can produce a square wave with an arbitrary duty cycle. Duty cycle is defined as the ratio of the period that the waveform is high to the total clock period. For example, a 40% duty cycle means that the square wave is high for 0.4×T<sub>period</sub> and low for 0.6×T<sub>period</sub>.

